506576310 03/25/2021

PATENT ASSIGNMENT COVER SHEET

Electronic Version v1.1 Stylesheet Version v1.2 EPAS ID: PAT6623089

SUBMISSION TYPE:	NEW ASSIGNMENT
NATURE OF CONVEYANCE:	ASSIGNMENT

CONVEYING PARTY DATA

Name	Execution Date	
ARM LIMITED	10/02/2020	

RECEIVING PARTY DATA

Name:	CERFE LABS, INC.
Street Address:	10621 OAK VIEW DRIVE
City:	AUSTIN
State/Country:	TEXAS
Postal Code:	78759

PROPERTY NUMBERS Total: 1

Property Type	Number
Application Number:	16940163

CORRESPONDENCE DATA

Fax Number:

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ATTORNEY DOCKET NUMBER:	394.P013C3
NAME OF SUBMITTER:	ELIZABETH COFFEE
SIGNATURE:	/Elizabeth Coffee/
DATE SIGNED:	03/25/2021

Total Attachments: 12

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> **PATENT** 506576310

REEL: 055724 FRAME: 0406

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> PATENT REEL: 055724 FRAME: 0407

ASSIGNMENT

This ASSIGNMENT ("ASSIGNMENT") is made and entered into by and between Arm Limited, a private limited company incorporated under the laws of England and Wales ("ASSIGNOR") and Cerfe Labs, Inc., a Delaware corporation ("ASSIGNEE"). This Assignment is made and entered into in connection with the consummation of the transactions contemplated by that certain Asset Purchase Agreement, dated as of October 2, 2020 by and between ASSIGNOR and ASSIGNEE (the "PURCHASE AGREEMENT"). For good and valuable consideration, the receipt and sufficiency of which are hereby acknowledged, ASSIGNOR and ASSIGNEE agree as follows:

- 1. ASSIGNOR hereby sells, assigns, and transfers to ASSIGNEE the entire worldwide right, title, and interest in the patent application(s) and patents listed in Schedule A hereto ("PATENT RIGHTS"):
- 2. ASSIGNOR hereby sells, assigns, and transfers to ASSIGNEE the entire worldwide right, title, and interest in and to: (a) the PATENT RIGHTS, including any right of priority; (b) any provisional, divisional, continuation, substitute, renewal, reissue, and other related applications thereto which have been or may be filed in the United States or elsewhere in the world; (c) any patents which may be granted on the applications set forth in (a) and (b) above; and (d) the right to sue in its own name and to recover for past infringement of any or all of any applications or patents issuing therefrom together with all rights to recover damages for infringement of provisional rights.
- 3. This ASSIGNMENT shall be construed and interpreted in accordance with the PURCHASE AGREEMENT. Nothing in this ASSIGNMENT shall, or shall be deemed to, modify or otherwise affect any provisions of the PURCHASE AGREEMENT or affect or modify any of the rights or obligations of the parties under the PURCHASE AGREEMENT. In the event of any conflict between the provisions hereof and the provisions of the PURCHASE AGREEMENT, the provisions of the PURCHASE AGREEMENT shall govern and control.
- 4. This ASSIGNMENT may be executed in one or more counterparts, each of which shall be deemed an original and all of which may be taken together as one and the same ASSIGNMENT.

Duly Authorized Representative of ASSIGNOR	Date of Signature
By: Jason Egal Name: Jason Egal	October 2, 2020
Title: EVP, Chief Strategy Officer	
Arm Limited	

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Duly Authorized Representative of ASSIGNEE	Date of Signature
By: Eric Hennenhoefer	October 2, 2020
Name: Eric Hennenhoefer	
Title: Chief Executive Officer/President	
Cerfe Labs, Inc.	

SCHEDULE A - PATENT RIGHTS

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
CeRAM Integration and Use as	China	Published	2016-	201680051800,3		
Programmable Fabric or High			09-07			
Density Crosspoint Array						
CeRAM Integration and Use as	European	Published	2016-	16770296.8		
Programmable Fabric or High	Patent	T GONSHOU	09-07	10770250.0		
Density Crosspoint Array	1 41.614		0,00			
CeRAM Integration and Use as	India	Published	2016-	201847012436		
Programmable Fabric or High	maru	1 donsiled	09-07	201017012130		
Density Crosspoint Array			0,0,			
CeRAM Integration and Use as	Japan	Application	2016-	2018-530978		
Programmable Fabric or High	Japan	ripplication	09-07	2010-330770		
Density Crosspoint Array			05-07			
CeRAM Integration and Use as	Korea,	Application	2016-	10-2018-7009852		
Programmable Fabric or High	Republic of	Application	09-07	10-2016-7009632		
Density Crosspoint Array	(KR)		09-07			
CeRAM Integration and Use as	United	Granted	2015-	14/848,129	2019	10,056,143
		Granted		14/848,129	2018-	10,036,143
Programmable Fabric or High	States of		09-08		08-21	
Density Crosspoint Array	America	C (1	2010	15/000 (04	2010	10.266.752
CeRAM Integration and Use as	United	Granted	2018-	15/999,694	2019-	10,366,753
Programmable Fabric or High	States of		08-20		07-30	
Density Crosspoint Array	America	*	2010	4.5/80.8.400		
CeRAM Integration and Use as	United	Published	2019-	16/525,432		
Programmable Fabric or High	States of		07-29			
Density Crosspoint Array	America					
Current Switchable CeRAM RC	China	Published	2016-	201680045146.5		
device			08-01			
Current Switchable CeRAM RC	European	Published	2016-	16751626.9		
device	Patent		08-01			
Current Switchable CeRAM RC	India	Published	2016-	201847006514		
device			08-01			
Current Switchable CeRAM RC	Japan	Application	2016-	2018-504847		
device			08-01			
Current Switchable CeRAM RC	Korea,	Application	2016-	10-2018-7005808		
device	Republic of		08-01			
	(KR)					
Current Switchable CeRAM RC	Taiwan	Granted	2016-	105124025	2020-	I694607
device			07-29		05-21	
Current Switchable CeRAM RC	United	Granted	2015-	14/815,054	2017-	9,735,766
device	States of	O TALLED	07-31	11,010,001	08-15	3,750,700
	America				** 10	
Current Switchable CeRAM RC	United	Published	2017-	15/659,288		
device	States of	1 donsiled	07-25	15/059,200		
device	America		0, 23			
Non-Symetric and Reverse-polar	China	Published	2016-	201680052536.5		
Switching in a CeRAM Device	Cinita	1 donsiled	09-09	201000032330.3		
Non-Symetric and Reverse-polar	Taiwan	Granted	2016-	105129236	2020-	I692201
Switching in a CeRAM Device	Taiwaii	Giaineu	09-09	103129230	04-21	1092201
	TInite 1	Cmnt-1		14/950 212	_	0.755.146
Non-Symetric and Reverse-polar	United	Granted	2015-	14/850,213	2017-	9,755,146
Switching in a CeRAM Device	States of		09-10		09-05	
N. G	America		201-	15/601.065	2010	10.01=01=
Non-Symetric and Reverse-polar	United	Granted	2017-	15/681,236	2019-	10,217,937
Switching in a CeRAM Device	States of		08-18		02-26	
	America				1	
Non-Symetric and Reverse-polar	United	Granted	2019-	16/284,901	2020-	10,763,433

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PATENT REEL: 055724 FRAME: 0410

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
Switching in a CeRAM Device	States of America		02-25		09-01	
Multiple Impedance CeRAM integration	China	Published	2016- 09-29	201680057845.1		
Multiple Impedance CeRAM integration	Taiwan	Application	2016- 09-30	105131576		
Multiple Impedance CeRAM integration	United States of	Granted	2015- 09-30	14/871,692	2018- 12-04	10,147,879
Carbon Doping of Transition Metal Oxide Films for CeRAM	America China	Application	2017- 01-25	201780008546.3		
Carbon Doping of Transition Metal Oxide Films for CeRAM	European Patent	Published	2017- 01-25	17707391.3		
Carbon Doping of Transition Metal Oxide Films for CeRAM	India	Published	2017- 01-25	201847031233		
Carbon Doping of Transition Metal Oxide Films for CeRAM	Japan	Application	2017- 01-25	2018-557220		
Carbon Doping of Transition Metal Oxide Films for CeRAM	Korea, Republic of (KR)	Application	2017- 01-25	10-2018-7024132		
Carbon Doping of Transition Metal Oxide Films for CeRAM	Taiwan	Application	2017- 01-26	106103151		
Carbon Doping of Transition Metal Oxide Films for CeRAM	United States of America	Granted	2016- 01-26	15/006,889	2017- 04-18	9,627,615
Carbon Doping of Transition Metal Oxide Films for CeRAM	United States of America	Granted	2017- 03-20	15/463,546	2018- 07-31	10,038,141
Oxidation Barrier Layer for CeRAM	China	Published	2017- 02-27	201780013869.1		
Oxidation Barrier Layer for CeRAM	United Kingdom	Published	2017- 02-27	1814731.4		
Oxidation Barrier Layer for CeRAM	Korea, Republic of (KR)	Published	2017- 02-27	10-2018-7026601		
Oxidation Barrier Layer for CeRAM	Taiwan	Published	2017- 02-24	106106323		
Oxidation Barrier Layer for CeRAM	United States of America	Granted	2016- 02-29	15/056,877	2017- 05-23	9,660,189
Oxidation Barrier Layer for CeRAM	United States of America	Granted	2017- 04-27	15/499,212	2018- 07-03	10,014,468
Nitrogen Based Doping of Correlated Electron Materials	China	Published	2017- 02-15	201780011895.0		
Nitrogen Based Doping of Correlated Electron Materials	United Kingdom	Published	2017- 02-15	1813620.0		
Nitrogen Based Doping of Correlated Electron Materials	Korea, Republic of (KR)	Published	2017- 02-15	10-2018-7026611		
Nitrogen Based Doping of Correlated Electron Materials	Taiwan	Published	2017- 02-16	106105049		
Nitrogen Based Doping of Correlated Electron Materials	United States of America	Published	2016- 02-17	15/046,177		
Varistor and Diode Based Access Devices for CeRAM	China	Published	2016- 12-20	201680075584.6		
Varistor and Diode Based Access Devices for CeRAM	European Patent	Application	2016- 12-20	16823308.8		
Varistor and Diode Based Access	India	Published	2016-	201847026437		

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
Devices for CeRAM			12-20			
Varistor and Diode Based Access Devices for CeRAM	Japan	Application	2016- 12-20	2018-532661		
Varistor and Diode Based Access Devices for CeRAM	Korea, Republic of (KR)	Application	2016- 12-20	10-2018-7020702		
Varistor and Diode Based Access Devices for CeRAM	Taiwan	Published	2016- 12-15	105141533		
Varistor and Diode Based Access Devices for CeRAM	United States of America	Granted	2015- 12-22	14/979,086	2017- 08-15	9,735,360
Varistor and Diode Based Access Devices for CeRAM	United States of America	Granted	2017- 07-10	15/645,061	2018- 11-20	10,134,987
Varistor and Diode Based Access Devices for CeRAM	United States of America	Granted	2018- 11-19	16/195,765	2020- 07-28	10,727,408
Method to Control Carbon in a Correlated Electron Material	China	Published	2017- 02-17	201780013466.7		
Method to Control Carbon in a Correlated Electron Material	United Kingdom	Published	2017- 02-17	1813622.6		
Method to Control Carbon in a Correlated Electron Material	Korea, Republic of (KR)	Published	2017- 02-17	10-2018-7027069		
Method to Control Carbon in a Correlated Electron Material	Taiwan	Application	2017- 02-17	106105209		
Method to Control Carbon in a Correlated Electron Material	United States of America	Published	2016- 02-19	15/048,778		
Oxidation Resistant Titanium Nitride Electrodes for CeRAM	China	Application	2017- 07-04	201780043177.1		
Oxidation Resistant Titanium Nitride Electrodes for CeRAM	Korea, Republic of (KR)	Application	2017- 07-04	10-2019-7003701		
Oxidation Resistant Titanium Nitride Electrodes for CeRAM	Taiwan	Published	2017- 07-11	106123165		
Oxidation Resistant Titanium Nitride Electrodes for CeRAM	United States of America	Granted	2016- 07-12	15/207,708	2019- 12-24	10,516,110
Oxidation Resistant Titanium Nitride Electrodes for CeRAM	United States of America	Published	2019- 12-23	16/725,907		
Fabrication of Correlated Electron Material Devices Method to Control Carbon	China	Published	2017- 02-17	201780012377.0		
Fabrication of Correlated Electron Material Devices Method to Control Carbon	United Kingdom	Published	2017- 02-17	1813623.4		
Fabrication of Correlated Electron Material Devices Method to Control Carbon	Korea, Republic of (KR)	Published	2017- 02-17	10-2018-7027057		
Fabrication of Correlated Electron Material Devices Method to Control Carbon	Taiwan	Published	2017- 02-17	106105200		
Fabrication of Correlated Electron Material Devices Method to Control Carbon	United States of America	Granted	2016- 02-19	15/048,244	2019- 01-01	10,170,700
Fabrication of Correlated Electron Material Devices Method to Control Carbon	United States of America	Granted	2016- 02-19	16/200,001	2020- 03-03	10,580,982

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
Alternate CeRAM Construction and Uses	China	Application	2017- 09-18	201780057712.9		
Alternate CeRAM Construction	European	Published	2017-	17772455.6	_	
and Uses	Patent	Published	09-18	1///2433.6		
Alternate CeRAM Construction	India	Published	2017-	201947008299		
and Uses	Illula	Fuonsieu	09-18	201947008299		
Alternate CeRAM Construction	Japan	Application	2017-	2019-515507	+	
and Uses	Јаран	Application	09-18	2019-313307		
Alternate CeRAM Construction	Korea,	Application	2017-	10-2019-7007482	_	
and Uses	Republic of (KR)	Application	09-18	10-2019-7007482		
Alternate CeRAM Construction and Uses	Taiwan	Published	2017- 09-19	106132059		
Alternate CeRAM Construction	United	Granted	2016-	15/270,974	2018-	9,978,942
and Uses	States of America		09-20		05-22	
Alternate CeRAM Construction	United	Granted	2018-	15/984,223	2019-	10,446,609
and Uses	States of America		05-18		10-15	
Alternate CeRAM Construction	United	Published	2019-	16/600,372		
and Uses	States of America		10-11			
Formation of Correlated Electron Material Device using UV Oxidation	China	Published	2017- 08-10	201780049967.0		
Formation of Correlated Electron	Taiwan	Published	2017-	106127436		
Material Device using UV Oxidation	Turvun	1 donsiled	08-14	100127430		
Formation of Correlated Electron	United	Granted	2016-	15/237,357	2019-	10,276,795
Material Device using UV	States of	Granica	08-15	10,237,307	04-30	10,270,750
Oxidation	America					
Doping Correlated Electron	China	Application	2017-	201780042126.7		
Material with Top or Bottom Electrode			07-04			
Doping Correlated Electron	Korea,	Application	2017-	10-2019-7003312		
Material with Top or Bottom Electrode	Republic of (KR)		07-04			
Doping Correlated Electron	Taiwan	Published	2017-	106122317		
Material with Top or Bottom Electrode			07-04			
Doping Correlated Electron	United	Granted	2016-	15/201,932	2018-	10,134,986
Material with Top or Bottom Electrode	States of America		07-05		11-20	
Doping Correlated Electron	United	Published	2018-	16/195,779		
Material with Top or Bottom Electrode	States of America		11-19			
Formation of Correlated Electron Switch using Delta Doping	China	Application	2017- 08-10	201780048726,4		
Formation of Correlated Electron Switch using Delta Doping	United Kingdom	Application	2017- 08-10	1902616.0		
Formation of Correlated Electron Switch using Delta Doping	Korea, Republic of (KR)	Application	2017- 08-10	10-2019-7005969		
Formation of Correlated Electron Switch using Delta Doping	Taiwan	Published	2017- 08-11	106127276		
Formation of Correlated Electron	United	Granted	2016-	15/234,854	2018-	9,997,702
Switch using Delta Doping	States of America		08-11	10,20 1,00 1	06-12	2,227,702
Formation of Correlated Electron	United	Granted	2018-	15/890,222	2019-	10,381,560
Switch using Delta Doping	States of		02-06	,	08-13	, ,
	America					

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
A Method for Making Nonvolatile Memories of the Strongly Correlated-electron (CeRAM) Type Using Chemical Stabilization of Metal-Ligand Defects by Ligand Substitution with Back Donation	China	Published	2017- 01-25	201780008557.1	2	
A Method for Making Nonvolatile Memories of the Strongly Correlated-electron (CeRAM) Type Using Chemical Stabilization of Metal-Ligand Defects by Ligand Substitution with Back Donation	European Patent	Published	2017- 01-25	17704524.2		
A Method for Making Nonvolatile Memories of the Strongly Correlated-electron (CeRAM) Type Using Chemical Stabilization of Metal-Ligand Defects by Ligand Substitution with Back Donation	India	Published	2017- 01-25	201847031224		
A Method for Making Nonvolatile Memories of the Strongly Correlated-electron (CeRAM) Type Using Chemical Stabilization of Metal-Ligand Defects by Ligand Substitution with Back Donation	Japan	Application	2017- 01-25	2018-557221		
A Method for Making Nonvolatile Memories of the Strongly Correlated-electron (CeRAM) Type Using Chemical Stabilization of Metal-Ligand Defects by Ligand Substitution with Back Donation	Korea, Republic of (KR)	Application	2017- 01-25	10-2018-7024129		
A Method for Making Nonvolatile Memories of the Strongly Correlated-electron (CeRAM) Type Using Chemical Stabilization of Metal-Ligand Defects by Ligand Substitution with Back Donation	Taiwan	Published	2017- 01-25	106102828		
A Method for Making Nonvolatile Memories of the Strongly Correlated-electron (CeRAM) Type Using Chemical Stabilization of Metal-Ligand Defects by Ligand Substitution with Back Donation	United States of America	Published	2016- 12-20	15/385,719		
Method for Making a Correlated Electron Material by Oxidation of a Metal Film	China	Application	2017- 11-30	201780074027.7		
Method for Making a Correlated Electron Material by Oxidation of a Metal Film	Taiwan	Published	2017- 11-30	106141783		
Method for Making a Correlated Electron Material by Oxidation of a Metal Film	United States of America	Granted	2016- 12-01	15/367,052	2019- 01-29	10,193,063
Method for Making a Correlated Electron Material by Oxidation of a Metal Film	United States of America	Published	2019- 01-28	16/259,917		
A Method for Creating Electrodes and Correlated Electron region in a Correlated Electron Material Device	China	Application	2017- 12-06	201780074610.8		
A Method for Creating Electrodes and Correlated Electron region in a Correlated Electron Material	Korea, Republic of (KR)	Application	2017- 12-06	10-2019-7018795		

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
Device						
A Method for Creating Electrodes and Correlated Electron region in a Correlated Electron Material Device	Taiwan	Published	2017- 12-06	106142658		
A Method for Creating Electrodes and Correlated Electron region in a Correlated Electron Material Device	United States of America	Granted	2016- 12-07	15/371,457	2019- 02-26	10,217,935
A Method for Creating Electrodes and Correlated Electron region in a Correlated Electron Material Device	United States of America	Published	2019- 02-25	16/284,932		
A Method for Integrating a CEM device	China	Application	2017- 12-05	201780073490.X		
A Method for Integrating a CEM device	European Patent	Application	2017- 12-05	17825276.3		
A Method for Integrating a CEM device	India	Published	2017- 12-05	201947024687		
A Method for Integrating a CEM device	Japan	Application	2017- 12-05	2019-528859		
A Method for Integrating a CEM device	Korea, Republic of (KR)	Application	2017- 12-05	10-2019-7018205		
A Method for Integrating a CEM device	Taiwan	Published	2017- 12-05	106142512		
A Method for Integrating a CEM device	United States of America	Granted	2016- 12-06	15/370,168	2019- 10-22	10,454,026
A Method for Integrating a CEM device	United States of America	Published	2019- 10-21	16/659,206		
Layered Correlated Electron Material for Switching Device	China	Published	2017- 08-04	201780051577.7		
Layered Correlated Electron Material for Switching Device	Taiwan	Published	2017- 08-22	106128369		
Layered Correlated Electron Material for Switching Device	United States of America	Granted	2016- 08-22	15/243,668	2020- 03-10	10,586,924
Metal wetting layer for metal compound CEM device formation	China	Application	2017- 12-18	201780076883.6		
Metal wetting layer for metal compound CEM device formation	Taiwan	Published	2017- 12-19	106144562		
Metal wetting layer for metal compound CEM device formation	United States of America	Published	2016- 12-19	15/383,926		
A Method	China	Published	2017- 08-25	201780056439.8		
A Method	Taiwan	Published	2017- 09-11	106130925		
A Method	United States of America	Granted	2016- 09-14	15/264,851	2018- 10-16	10,103,327
A Method	United States of America	Granted	2016- 09-14	16/160,291	2019- 09-03	10,403,816
Chemical Signature for CEM Devices	China	Published	2017- 08-18	201780054201.1		
Chemical Signature for CEM	European	Published	2017-	17758910.8		

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
Devices	Patent		08-18	Trumper	Date	
Chemical Signature for CEM Devices	India	Published	2017- 08-18	201917005054		
Chemical Signature for CEM Devices	Japan	Published	2017- 08-18	2019-512983		
Chemical Signature for CEM Devices	Korea, Republic of (KR)	Published	2017- 08-18	10-2019-7004987		
Chemical Signature for CEM Devices	Taiwan	Published	2017- 09-08	106130755		
Chemical Signature for CEM Devices	United States of America	Granted	2016- 09-09	15/260,515	2018- 11-13	10,128,438
Chemical Signature for CEM Devices	United States of America	Granted	2016- 09-09	16/169,372	2020- 05-19	10,658,587
CeRAM Device Structures for High Yield Integration	China	Published	2018- 01-23	201880007258.0		
CeRAM Device Structures for High Yield Integration	Korea, Republic of (KR)	Published	2018- 01-23	10-2019-7022847		
CeRAM Device Structures for High Yield Integration	Taiwan	Published	2018- 01-23	107102322		
CeRAM Device Structures for High Yield Integration	United States of America	Granted	2017- 01-24	15/414,520	2018- 11-27	10,141,504
CeRAM Device Structures for High Yield Integration	United States of America	Granted	2018- 11-26	16/200,214	2020- 07-07	10,707,415
Electrode Liner for CEM Devices	Taiwan	Published	2017- 11-28	106141303		
Electrode Liner for CEM Devices	United States of America	Granted	2016- 11-29	15/363,216	2018- 11-06	10,121,967
Electrode Liner for CEM Devices	United States of America	Granted	2018- 10-24	16/169,114	2020- 07-28	10,727,406
TMO based non-polar BEOL diode and access device	China	Application	2018- 05-30	201880033755.8		
TMO based non-polar BEOL diode and access device	Korea, Republic of (KR)	Application	2018- 05-30	10-2019-7038146		
TMO based non-polar BEOL diode and access device	Taiwan	Published	2018- 05-30	107118436		
TMO based non-polar BEOL diode and access device	United States of America	Granted	2017- 05-31	15/610,288	2019- 07-02	10,340,453
TMO based non-polar BEOL diode and access device	United States of America	Granted	2019- 07-01	16/459,518	2020- 06-30	10,700,280
Surface Stoichiometry for CeRAM	China	Published	2018- 06-28	201880044924.8		
Surface Stoichiometry for CeRAM	Korea, Republic of (KR)	Published	2018- 06-28	10-2019-7038309		
Surface Stoichiometry for CeRAM	United States of America	Granted	2017- 07-03	15/641,143	2019- 02-19	10,211,398
Surface Stoichiometry for CeRAM	United States of	Granted	2017- 07-03	16/261,413	2020- 03-17	10,593,880

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
	America					
Methods of making a correlated electron device	China	Published	2018- 07-03	201880043755.6		
Methods of making a correlated electron device	Korea, Republic of (KR)	Application	2018- 07-03	10-2020-7002218		
Methods of making a correlated electron device	Taiwan	Published	2018- 07-02	107122806		
Methods of making a correlated electron device	United States of America	Published	2017- 07-03	15/641,124		
Methods of making a correlated electron device	United States of America	Application	2020- 07-23	16/937,403		
Integration of CeRAM films for optimal performance	Taiwan	Published	2019- 03-28	108110846		
Integration of CeRAM films for optimal performance	United States of America	Published	2018- 03-28	15/939,160		
Integration of CeRAM films for optimal performance	Patent Cooperation Treaty	Application	2019- 03-21	PCT/GB2019/050804		
Method of forming a CeRAM	Taiwan	Application	2019- 03-28	108110918		
Method of forming a CeRAM	United States of America	Granted	2018- 03-28	15/939,183	2019- 09-17	10,418,553
Method of forming a CeRAM	United States of America	Published	2019- 09-16	16/572,521		
Method of forming a CeRAM	Patent Cooperation Treaty	Application	2019- 03-21	PCT/GB2019/050796		
CeRAM as a Synapse or a Neuron for brain-based computing	China	Application	2019- 01-11	201980015833.6		
CeRAM as a Synapse or a Neuron for brain-based computing	Taiwan	Published	2019- 01-21	108102231		
CeRAM as a Synapse or a Neuron for brain-based computing	United States of America	Published	2018- 01-31	15/884,612		
CeRAM as a Synapse or a Neuron for brain-based computing	Patent Cooperation Treaty	Published	2019- 01-11	PCT/GB2019/050080		
Ligand based Correlated electron device	Taiwan	Application	2020- 08-17	109127869		
Ligand based Correlated electron device	United States of America	Application	2019- 09-12	16/569,495		
Ligand based Correlated electron device	Patent Cooperation Treaty	Application	2020- 08-25	PCT/GB2020/052038		
CeRAM top metal contact integration to reduce parasitic capacitance	Korea, Republic of (KR)	Application	2019- 02-28	10-2020-7026279		
CeRAM top metal contact integration to reduce parasitic capacitance	Taiwan	Published	2019- 03-22	108110011		
CeRAM top metal contact integration to reduce parasitic capacitance	United States of America	Granted	2018- 03-23	15/933,747	2020- 02-18	10,566,527

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CeRAM top metal contact integration to reduce parasitic	Patent Cooperation	Published	2019- 02-28	PCT/GB2019/050559		
capacitance	Treaty					
Dual Damascene contact to CeRAM	Taiwan	Application	2019- 09-02	108131462		
Dual Damascene contact to CeRAM	United States of America	Published	2019- 02-08	16/271,377		
Dual Damascene contact to CeRAM	Patent Cooperation Treaty	Published	2019- 02-21	PCT/GB2019/050479		
Process integrations for CeRAM sidewall protection and restoration	Korea, Republic of (KR)	Application	2019- 02-28	10-2020-7026281		
Process integrations for CeRAM sidewall protection and restoration	United States of America	Published	2018- 03-23	15/933,818		
Process integrations for CeRAM sidewall protection and restoration	Taiwan	Published	2019- 03-22	108109985		
Process integrations for CeRAM sidewall protection and restoration	Patent Cooperation Treaty	Published	2019- 02-28	PCT/GB2019/050562		
CeRAM integration to prevent shunting short	United States of America	Published	2018- 10-17	16/163,246		
Alternative interconnect integration for making contact to CeRAM pillars	United States of America	Granted	2018- 11-30	16/206,725	2020- 06-02	10,672,982
Alternative interconnect integration for making contact to CeRAM pillars	United States of America	Application	2020- 06-02	16/890,881		
Alternative interconnect integration for making contact to CeRAM pillars	Patent Cooperation Treaty	Published	2019- 11-15	PCT/GB2019/053257		
A Method to Design Transition Metal Oxides Suitable for Metal Insulator Transition Mott Like Memories and Switches	United States of America	Granted	2018- 08-07	16/057,515	2020- 03-03	10,580,981
A Method to Design Transition Metal Oxides Suitable for Metal Insulator Transition Mott Like Memories and Switches	United States of America	Published	2018- 08-07	16/750,168		
A Method to Design Transition Metal Oxides Suitable for Metal Insulator Transition Mott Like Memories and Switches	Patent Cooperation Treaty	Published	2019- 07-31	PCT/GB2019/052144		
Bizmuth doping to achieve ferroelectric behavior in TMO, PTMO, TMC and PTMC but with an emphasis on HfO as the primary material of choice	United States of America	Application	2019- 01-15	16/248,496		
Bizmuth doping to achieve ferroelectric behavior in TMO, PTMO, TMC and PTMC but with an emphasis on HfO as the primary material of choice	Patent Cooperation Treaty	Application	2019- 12-23	PCT/GB2019/053688		
Configurable Josephson Junction with non-volatility	United States of America	Application	2020- 02-13	16/790,729		
Hydrogen barrier for CeRAM integration	United States of	Application	2019- 05 - 09	16/408,452		

Patent Application Title	Country	Status	Filed Date	Application Number	Grant Date	Patent No.
	America					
Hydrogen barrier for CeRAM integration	Patent Cooperation Treaty	Application	2020- 03-12	PCT/GB2020/050630		
Morphology Enhanced Correlated Electron Switch	United States of America	Application	2020- 04-29	16/862,428		
Dopant activation anneal for CeRAM	Taiwan	Application	2020- 08-17	109127860		
Dopant activation anneal for CeRAM	United States of America	Application	2019- 08-28	16/554,385		
Dopant activation anneal for CeRAM	Patent Cooperation Treaty	Application	2020- 08-19	PCT/GB2020/051980		
Method to adjust Ni/O ratio to create active CERAM device layer	United States of America	Application	2020- 04-16	16/850,875		
Novel CeRAM stack to enhance single polar switching	United States of America	Application	2020- 01-21	16/748,555		

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